

2N6151-2N6153

High-reliability discrete products and engineering services since 1977

SILICON BIDIRECTIONAL THYRISTORS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|---------------------|-------------|------------------|
| Repetitive Peak Off-Stage Voltage, Gate Open | | | |
| 2N6151 | V _{DRM} | 200 | Volts |
| 2N6152 | V DRM | 400 | VOILS |
| 2N6153 | | 600 | |
| RMS On-State Current (T _c = 80°C) | I _{T(RMS)} | 10 | Amps |
| Peak Non-Repetitive Surge Current (One Cycle, 60Hz) | I _{TSM} | 100 | Amps |
| Circuit Fusing Considerations | l ² t | | A ² s |
| (t = 8.3ms) | 1-t | 60 | A-S |
| Peak Gate Power (T _J = 75°C, pulse width = 2.0µs) | Р _{бм} | 20 | Watts |
| Average Gate Power (T _J = 75°C, t = 8.3ms) | P _{G(AV)} | 0.5 | Watts |
| Peak Gate Current (pulse width = 10µs) | I _{GM} | 2.0 | Amps |
| Peak Gate Voltage | V _{GM} | 10 | Volts |
| Operating Junction Temperature Range | TJ | -40 to +100 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

THERMAL CHARACTERISTICS

| Characteristics | Symbol | Max | Unit |
|--------------------------------------|------------------|-----|------|
| Thermal Resistance, Junction To Case | Rejc | 2.0 | °C/W |
| Thermal Resistance, Case To Ambient | R _{OCA} | 50 | °C/W |

ELECTRICAL CHARACTERISTICS (T_c = 25°C and either polarity of MT2 to MT1 voltage unless otherwise noted)

| Characteristic | | Min | Тур | Max | Unit |
|---|-----------------|-----|-----|------|-------|
| Peak Off State Current | | | | | |
| (V _D = V _{DRM} , gate open) | | | | | mA |
| T _c = 25°C | DRM | - | - | 0.1 | IIIA |
| Tc = 100°C | | - | - | 0.5 | |
| Peak On-State Voltage | N | | | | Volts |
| (I_{TM} = 14A peak, pulse width \leq 1 ms, duty cycle \leq 2%) | V _{TM} | - | - | 1.65 | VOITS |
| Critical Rate Of Rise Of Off-State Voltage | du /d+ | | | | Mus |
| (V_D = Rated V_{DRM} , gate open, exponential waveform, T_C = 100°C) | dv/dt | - | 50 | - | V/µs |
| Critical Rate Of Rise Of Commutating Voltage | | | | | |
| ($I_{T(RMS)}$ = Rated $I_{T(RMS)}$, V_D = Rated V_{DRM} , commutating di/dt = 5.4A/ms, gate open, T_C = 80°C) | dv/dt(c) | 4 | - | - | V/µs |
| DC Gate Trigger Current (continuous dc) | | | | | |
| (V _D = 12V, trigger mode) | | | | | |
| MT2(+), G(+); MT2(-), G(-); R _L = 100Ω | I _{GT} | | - | 50 | mA |
| MT2(+), G(-); R_L = 50 Ω | | | - | 50 | IIIA |
| MT2(+), G(+); MT2(-), G(-); R _L = 50Ω, T _C = -40°C | | - | - | 80 | |
| MT2(+), G(-);R _L = 25Ω, T _C = -40°C | | - | - | 80 | |



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ELECTRICAL CHARACTERISTICS ($T_c = 25^{\circ}C$ and either polarity of MT2 to MT1 voltage unless otherwise noted)

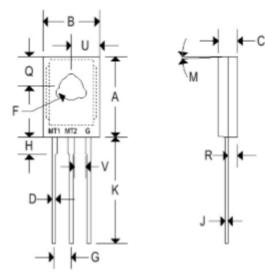
| Characteristic | Symbol | Min | Тур | Max | Unit |
|---|-----------------|-----|-----|-----|-------|
| DC Gate Trigger Voltage (continuous dc) | V _{GT} | | | | Volts |
| (V _D = 12V, trigger mode) | | | | | |
| MT2(+), G(+); MT2(-), G(-); R _L = 100Ω | | - | - | 2.5 | |
| MT2(+), G(-);RL = 50Ω | | - | - | 2.5 | |
| MT2(+), G(+); MT2(-), G(-); R _L = 50Ω, T _C = -40°C | | - | - | 3.5 | |
| MT2(+), G(-);R _L = 25Ω, T _C = -40°C | | - | - | 3.5 | |
| (V_D = Rated V_DRM, R_L = 1000 \Omega, T_C = 100 °C) all polarities | | 0.2 | - | - | |
| Holding Current | Iн | | | | mA |
| (V _D = 24V, I_T = 0.5A, pulse width = 1ms, duty cycle \leq 2%, | | | | | |
| gate trigger source 7V, 20Ω) | | | | | |
| T _c = 25°C | | - | - | 50 | |
| T _c = -40°C | | - | - | 100 | |
| Latching Current | IL. | | | | mA |
| (V _D = 24V) | | | | | |
| Trigger source: 15V, 100 Ω , trigger mode) | | | | | |
| MT2(+), G(+); MT2(-), G(-) | | - | - | 100 | |
| MT2(+), G(-) | | - | - | 200 | |
| MT2(+), G(+); MT2(-), G(-), T _c = -40°C | | - | - | 200 | |
| MT2(+), G(-), T _c = -40°C | | - | - | 400 | |



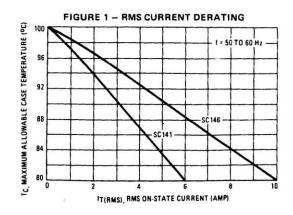
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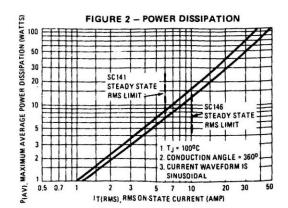
MECHANICAL CHARACTERISTICS

| Case | TO-127 |
|---------|---------------|
| Marking | Alpha-numeric |
| Pin out | See below |



| | | TO. | -127 | | |
|---|-----------|-------|--------|----------|--|
| | Inc | hes | | neters | |
| | Min | Max | Min | Max | |
| Α | 0.635 | 0.645 | 16.130 | 16.380 | |
| В | 0.495 | 0.505 | 12.570 | 12.830 | |
| C | 0.125 | 0.135 | 3.180 | 3.430 | |
| D | 0.043 | 0.049 | 1.090 | 1.240 | |
| F | 0.138 | 0.148 | 3.510 | 3.760 | |
| G | 0.166 BSC | | 4.220 | .220 BSC | |
| Н | 0.105 | 0.115 | 2.670 | 2.920 | |
| J | 0.032 | 0.034 | 0.813 | 0.864 | |
| K | 0.595 | 0.645 | 15.110 | 16.380 | |
| Μ | 9.1 | ΓYP | 9° 1 | ΓYP | |
| Q | 0.185 | 0.195 | 4.700 | 4.950 | |
| R | 0.075 | 0.085 | 1.910 | 2.160 | |
| U | 0.245 | 0.255 | 6.220 | 6.480 | |
| ٧ | 0.080 | - | 2.030 | - | |





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